# First-principles study of adhesion at Cu/SiO<sub>2</sub> interfaces

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The structural, electronic, and adhesive properties of Cu/SiO<sub>2</sub> interfaces are investigated using rstprinciples density-functional theory within the local density approximation. Interfaces between fcc Cu and -cristobalite (001) surfaces with di erent surface stoich iom etries are considered. Interfacial properties are found to be sensitive to the choice of the term ination, and the oxygen density at the substrate surface is the most important factor in uencing the strength of adhesion. For oxygenrich interfaces, the O atom s at the interface substantially rearrange after the deposition of Cu layers, suggesting the formation of Cu-O bonds. Signi cant hybridization between Cu d and O p states is evident in site-projected density of states at the interface. As oxygen is systematically rem oved from the interface, less rearrangement is observed, in plying weaker adhesion. C om puted adhesion energies for each of the interfaces are found to re ect these observed structural and bonding trends, leading to the largest adhesion energy in the oxygen rich cases. The adhesion energy is also calculated between Cu and SiO<sub>2</sub> substrates term inated with hydroxylgroups, and adhesion of Cu In s can adhere well to hydroxyl-free SiO<sub>2</sub> substrates should oxygen be present in su cient am ounts at the interface.

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I. IN TRODUCTION

A dhesion of thin m etal Im s to glass substrates have continued to be the subject of intense study for m any years because of its importance to the large-area electronics industry. Copper in particular, a noble m etal with a high bulk therm all and electrical conductivities, and apparently low electrom igration rate,<sup>1</sup> is an excellent candidate for interconnects in integrated circuitry on dielectric substrates, and thus the form ation of a strong and highly reliable interface between copper and glass has been an issue of prim ary importance. Unfortunately, Cu

In s are often reported to bind rather poorly to oxidebased glass substrates,  $2^{15}$  and Im s that do adhere at room tem perature can show dim inished adhesivity after therm al cycling,<sup>8;12</sup> an e ect often attributed to di erences of therm al expansion between Cu and the oxide substrate.<sup>8</sup> In m any studies, poor bonding is frequently explained by noting that since Cu does not reduce  $SiO_{2}$ , a graded oxide layer facilitating the adhesion is unable to form. Chem ically, copper possesses a half-empty s shell and a reasonably tightly-bound and led d-shell, and thus is less reactive than alum inum and many transition metal  $\lim s_r^2$  which oxidize well and are observed to adhere more reliably. Thus it is not surprising that adhesion is often in proved experim entally by applying transition m etal interm ediary layers  $^{6;8}$  prior to Cu  $\,$  lm deposition, or alloying the Cu Im s with sm all am ounts ofM g or A L<sup>4;5;9 {12}</sup>

A dhesion of copper Im s to oxide glasses is, of course, expected to be highly sensitive to the tem perature, oxygen partial pressure, and the condition of the glass surface prior to deposition. A common feature of many studies of Cu lm s on glass is that they were performed under conditions amenable to surface passivation either before or during deposition of the copper lm. For example, Cu

In s sputtered under high purity conditions in a vacuum do adhere to glass substrates.<sup>5;7;8</sup> In particular, O hm i et al.<sup>7</sup> dem onstrated robust adhesion of copper to glass after rem oving hydroxyl (O H) groups from the interface in situ just prior to deposition. This suggests that dangling bonds at m oisture-free glass surfaces would be readily saturated by Cu-O bonds.

G lasses in portant to industry can be chem ically com plex, often containing a substantial amount (perhaps

30%) of alum inum, boron, and other alkaline earth elements. Their primary component, however, is alm ost always  $SiO_2$ , which by itself form s one of the sim plest glasses, an orphous silica  $(a-SiO_2)$ . In the interest of sim plifying the chem istry, we shall restrict our focus to chem ically-pure SiO<sub>2</sub> glasses for the duration of this study. Am orphous silica has no long range order yet remarkably, on length scales comparable to a SiO bond, it is nearly perfectly ordered: the bond-length does not vary appreciably from 1.61 A; each Siatom is tetrahedrally coordinated with 0 atom s, and the bonds are primarily of a covalent nature. At length scales between 5 A and 8 A, m in im al variations in O-SiO and SiO-Si bond angles result in an appreciable degree of interm ediate range orientational disorder. P revious work using moleculardynam icshasbeen perform ed on both bulk vitreous silica and silica surfaces.<sup>16 {20</sup> M uch of it was based on sem i-em pirical potentials,<sup>16 {19</sup> which though able to simulate systems large enough to correctly capture the e ects of the interm ediate range orientational disorder, are expected to be far less accurate when local conditions deviate from those in the bulk, such as they do at surfaces or interfaces.

Since microscopically adhesion is related to the strength of the electronic bond between atom s at the interface, the bcalelectronic structure at the interface will play an important role in understanding the reactivity of the metal with the oxide substrate. A rst principles treatment would therefore be most appropriate for exam ining the nature of local bonding at an ideal interface between the two systems, and indeed this approach has proved insightful in the past for studying adhesion between metal Im s and insulating substrates.<sup>21{24</sup> P revious rst-principles work on the quartz surface<sup>20</sup> observed signi cant changes in bonding near the surface; to our know ledge, how ever, the e ects of m etallic overlayers on SiO<sub>2</sub> surface geom etries and electronic properties have yet to be examined from st principles.

In this article, we assess the degree to which the chem ical bonding at atom ically-sharp interfaces re ects the empirical trends in the adhesion of metallic contacts to glass substrates through study of a sim pli ed system, Cu m onolayers on cristobalite, a crystalline SiO 2 polymorph which although ordered does possess a density quite close to that of a-SiO  $_2$ .<sup>25</sup> A dhesion is studied as a function of oxygen surface coverage from st principles, using density functional theory within the local density approximation (LDA).<sup>26</sup> Our methods allow us to elucidate the role of local chem istry in binding the lm to glass, but require us to neglect its inherent long-range disorder and also, to a limited extent, its interm ediate-range orientational disorder. Since we are chie y interested in the local bonding properties, which are expected to be the same for both am orphous and crystalline silica, the loss of disorder is acceptable. W e sum m arize the m ethod and approximations used here in Sec. II; in Sec. III we describe the relaxed 1 1 -cristobalite (001) surfaces considered here, which include both stoichiom etric and nonstoichiom etric surface term inations, chosen so as to re-

ect di erent possible oxygen coverages that m ay result from di erent deposition conditions. In Sec. IV, we detail results of atom ic relaxation of  $Cu/SiO_2$  interfaces, where the adhesion is found to be critically sensitive to oxygen density at the substrate surface, and where relatively strong bonding is reported for oxygen-rich surfaces. The e ect of hydroxyl groups as a surface passivator is also brie y considered by calculating adhesion energies between copper m onolayers and a hydroxyl-term inated SiO<sub>2</sub> surface. A fler discussing our results and their im - plications, we provide concluding rem arks in Sec.V.

# II.M ETHODOLOGY

### A.Com putational details

Our rst-principles density-functional calculations are carried out within the LDA, using the correlation energy of Ceperley and Alder,<sup>27</sup> as in plan ented within the Vienna ab initio Simulation Program<sup>28 {30</sup> (VASP). We use a plane-wave basis set with a 29 Ry cut-o, and ultrasoft pseudopotentials<sup>31;32</sup> for Cu and H, projector augmented-wave potentials<sup>33;34</sup> for 0, and a norm conserving pseudopotential35 for Si. The Monkhorst-Pack k point mesh is chosen so that  $n_k = 3$ 3 1 for the 5 A 5 A 30 A supercell which is used in this work. A lso, we make use of a Ferm i-distribution sm earing with the tem perature of  $k_B T$ 02 eV to facilitate rapid convergence. These com putational conditions provide good convergence of the structure, density of states, and energy di erences given here, and are used throughout this work unless otherwise stated.

It should be mentioned that the k point sampling discussed above is not entirely su cient for study of the bulk properties of copper. In fact, the total energy of bulk copper obtained with this sampling is converged to about 0.02 eV per Cu atom. However, a sparser mesh turns out to be adequate for this study since energy differences are converged. To demonstrate, we increased our sampling to  $n_k = 4$  4 1 for the supercell mentioned above, recalculated total energies and forces, and found that the resulting di erence in adhesion energy is less than 4% even in the largest case.

### B.Bulk properties of constituent system s

Copper crystallizes in the fcc structure under norm al conditions and its lattice constant is 3.615 A at 291 K.<sup>36</sup> The LDA underestimates this lattice constant as is well known, and we obtain 3.532 A for the equilibrium value as shown in Table I, in agreem ent with a previous LDA study.<sup>39</sup> At equilibrium we nd a = 4.975A and c = 6.907 A for the tetragonal cell of bulk -cristobalite (the  $P 4_1 2_1 2$  structure), in excellent agreement with experiment<sup>38</sup> and previous LDA calculations.<sup>40;41</sup> Further, the computed Si-O bond length ( 1:606 A) is rem arkably close to experiment ( 1:603 A), and the calculated 0-Si-O bond angle is near the tetrahedral ideal value, also in-line with m easurem ent.<sup>38</sup> C onveniently, the choice of -cristobalite circum vents spurious lattice m ism atch when considering the interfaces with Cu overlayers: gom pare the lattice constant a of cristobalite with 2a of Cuin Table I.

TABLE I. Lattice constants of Cu and -cristobalite observed in experiment and LDA calculation.<sup>37</sup> W ycko positions, two SiO bond lengths, and four O-SiO bond angles are also shown for -cristobalite; the SiW ycko position (4a) is shown as (u;u;0) and the O W ycko position (8b) as (x;y;z). The experimental data are taken from R efs. 36 and 38 for copper and -cristobalite, respectively.

		Experiment	Thiswork (LDA)
Cu	a (A)	3.615	3.532
	<sup>P</sup> <u>-</u> 2a (A)	5.112	4.995
-cristobalite	a (A)	4.972	4.975
	с(А)	6.922	6.907
	u (Si)	0.3003	0.3005
	х (О)	0.2392	0.2389
	у (О)	0.1044	0.1058
	z (O)	0.1787	0.1801
	SiO (A)	1.6026	1.6056
	Si-O (A)	1.6034	1.6062
	0-si0 ()	109.0	108.3
	0-si0 ()	110.0	109.9
	0-si0 ()	108,2	108.8
	0-SiO ()	111.4	111.7

### III. (001) SURFACES OF CRISTOBALITE SIO 2

As a starting point, we consider an cristobalite slab consisting of 5 SiO  $_2$  layers, the thickness of which is

8.3 A. Translational symmetry is removed along the c-axis, de ning two di erent (001) surfaces perpendicular to this axis. We embed this -cristobalite slab, along with about 20 A of vacuum, within a supercell having dimensions of 5 A 5 A 30 A.O xygen number at the top of our SiO<sub>2</sub> slab is then changed to m in ic di erent substrate term inations. Two nonbridging oxygen atom s term inate the bottom of the slab, and two additional H atom s are attached to the oxygens to rem ove dangling bonds. Forces on the atom s are computed using the Hellm ann-Feynm an theorem , and the positions of atom s are then updated until the total energy reaches a minin um. The oxygen atoms at the bottom surface, term inated by hydrogens, are xed at their bulk positions in order to reduce size e ects owing to the nite thickness of the SiO  $_2$  slab, though the positions of each of the hydrogen atom s are permitted to relax. Previous rstprinciples calculations of -quartz surfaces<sup>20</sup> and model.  $Si/SiO_2$  interfaces<sup>42</sup> have indicated that about 5 A away from the interface, the local structural and electronic properties of the slab are bulk-like, and thus the size of our slab is su cient to approxim ate both surface and buk features.

Figure 1 presents views of the relaxed -cristobalite (001) surfaces. Supercells with slabs having three di erent surface term inations are considered in this work, which we label as  $Si_{-}, O_{-}$ , and  $OO_{-}$  term inated. The Siterm inated slab contains ve  $SiO_{2}$  units together



FIG.1. Relaxed structures of the  $\ - {\rm cristobalite}\,(001)$  surfaces.

with two bottom hydrogens; the O-term inated slab is identical to the Si-term inated except that the dangling surface oxygen atom is added; the 00 -term inated slab is again a modi cation of the Siterm inated slab in which two oxygens are added to the surface. Bond lengths and angles are not expected to rem ain bulk-like at the surface, where the choice of term ination can leave non-bridging oxygens with dangling bonds at the surface (e.g., in the 00-term inated cases). Indeed, we nd that relaxation signi cantly changes the SiO bond lengths within two atom ic layers from the surface for all term inations considered, and the nature of these changes is strongly dependent on the term ination. In the Siterm inated case, the additional charge carried by the dangling Sibonds forces the Sisurface atom above the plane of the surface; as a result the Si-O bonds supporting it from below elongate slightly to 1.64 A. In the O-term inated case, the surface O atom, bonded to only one other Si, relaxes downward into the surface, and its bond length decreases by more than 5% from 1.6 A to 1.5 A. In the 00-term inated case, in some contrast to the Si- and O -term inated slabs, the SiO bond lengths remain essentially the same as bulk. But the distance between 0 neighbors on the surface is also 1.6 A, which is very sm all compared with typical bulk 0 second neighbordistances of 2.7 A. Thus 0 atom sm ay evidently saturate dangling bonds through bonding with neighboring 0 atom s at this surface.

As expected, the total cohesive energies of the supercells decrease substantially with each additionalO atom : adding one oxygen atom or two oxygen atoms lowers the cohesive energy by 7.1 eV or 11.3 eV per surface Si, respectively. Since the energy required to break the  $O_2$  bond is nearly 5 eV per molecule, this energy com parison suggests that the OO-term inated surface m ay be the most stable of the three term inations, and the O-term inated surface the second. Evidently our rstprinciples calculations are consistent with the intuition that glass surfaces should be oxygen-rich.



FIG.2. Relaxed structures of the Cu/ -cristobalite(001) interfaces.

### IV.CU/SIO<sub>2</sub> IN TERFACES: RESULTS AND D ISCUSSION

### A . Interfacial structure

We now add ve Cu layers to each of the fully-relaxed (001) -cristobalite surfaces, obtained as discussed above in Sec. III. The Cu layers are initially positioned on the surface so that a C u atom in the low est m on o layer lies on the form er sym m etry axis of the -cristobalite slab. The length of the supercell lattice vector norm alto the surface (the c-axis) is xed to 30A as in Sec. III, a value we nd to be large enough to accom m odate up to ve additional Cu layers while keeping the interactions between the surfaces in neighboring supercells m in im al. Each m onolayer in our supercell contains four Cu atom s, and before relaxation each Cu atom has four intralayer neighbors at a distance of 2.5 A. Fortunately, the lattice parameter of the 1 pl\_suppace of -cristobalite is wellm atched to that ofthe 2 2 surface of copper as shown in Table I (the m ism atch is less than 1%). The sm all lattice m ism atch is artifact of our approxim ate treatm ent of am orphous silica as crystalline. In reality, stress induced by latticem atching is relieved through form ation of defects and/or dislocations. (In the case of a truly am orphous substrate, stress m ay also be overcom e through surface reconstruction, a complexity we neglect in the present work.)

The positions of all atom s in the supercell are again relaxed except for the bottom 0 atom s, and Fig.2 shows s the optim ized structures of the interfaces for each term ination. The most signi cant reconstruction at the interface is observed in the 00-term inated case. The 0-0 bond observed at the free -cristobalite surface in Fig. 1 is broken by the deposition of copper, and the 0-Si-0 angle is changed from 59 to 104 with the Si-0 bond lengths kept alm ost constant. This large rearrangem ent would indicate bond form ation between interfacial 0 and Cu atom s, suggesting good chem ical adhesion between the oxide substrate and the Cu Im. Each interfacial 0 atom has two Cu neighbors, and the Cu-0 bond lengths are computed to be 1:9 A, strikingly sim ilar to



FIG.4. Change in electron density h n(z)i (see text) as a function of the depth z from the substrate surface. The positions of each atom are designated by open circles for Si, solid circles for O, open squares for Cu, and open triangles for H.

Cu-O distances found in cuprates,  $^{43}$  where each copper atom is coordinated by four oxygens and considered to be in a Cu<sup>2+</sup> state. Sim ilar Si-O and Cu-O bond lengths are observed at the interface between O -term inated surfaces and Cu m onolayers, although the Si-O-Cu angles are sm aller than in the OO -term inated case by 15, as can be seen in Fig. 2. The m agnitude of the reconstruction at the O -term inated/Cu interface is less than that at the OO -term inated/Cu interface.

The interface between the Siterm inated substrate and Cu is completely di erent from either of the oxygen term inated interfaces. In this case, the interfacial Si atom possesses four Cu neighbors, each with bond length

2:4 A, and there is negligible atom ic rearrangement, im plying more metallic-like bonding.

#### B.Electronic properties

To investigate further the bonding properties of each interface discussed above, we compute the site-projected local density of states (LDOS) for atoms near the interfaces, and compare them with those obtained for bulk-like atoms deeper inside the slabs; the LDOS are shown together for each interface in Fig. 3. In the OO-term inated case, signi cant hybridization is observed between Cu d and O p states just below the Ferm i level. A key feature is the slight bump in the O p LDOS, lying about 1 eV below the Ferm i energy, which becomes



FIG.3. Local density of states (LDOS) projected by site and angular momentum. The solid lines show the LDOS of atoms at (or near) the interfaces, and the dashed lines show those of atoms in the middle of the slabs (the LDOS of an approximate bulk material). When computing the LDOS, a gaussian smearing method is used with = 0.2 eV. The sphere sizes of each atom are taken as 1.11 A for Si, 0.73 A for O, and 1.38 A for Cu.

progressively smaller with decreasing 0 content at the interface, and nearly vanishes in the Sitem inated case. Evidently strong hybridization between Cu d and O p states is responsible for the signi cant reconstruction at the 00-interface. It is worth pointing out here that as the number of 0 atoms at the interface is decreased, the Si sp LDOS around the Ferm i energy increases, that is the interfacial bonding takes on a more metallic character. This behavior results from the hybridization of Si sp states with the itinerant Cu s states around the Ferm i energy. In addition, we observe the bandgap com puted within the LDA (an underestimate of the true bandgap) opens and gradually approaches its bulk LDA value for LDOS in the middle of the SiO $_2$  slab, con rm ation that our slab exhibits approxim ate bulk behavior away from the interface.

To exam ine the degree to which changes in structural and bonding properties are conned to the interface, and to observe the mixing between the electronic states of the SiO<sub>2</sub> substrate and the Cu layers in more detail, we calculate the density dimension from the superposition, namely,

$$h n (z)i = hn_{IF} (z)i [hn_{SiO_2} (z)i + hn_{Cu} (z)i];$$

where  $m_{\rm IF}$  (z)i,  $m_{\rm SD_2}$  (z)i, and  $m_{\rm Cu}$  (z)i are the densities of the Cu/SiO<sub>2</sub> interface, the SiO<sub>2</sub> substrate, and the Cu layers, respectively, averaged over the xy plane (parallel to the interface). To obtain  $m_{\rm SiO_2}$  (z)i ( $m_{\rm Cu}$  (z)i), we simply remove the Cu layers (SiO<sub>2</sub> substrate) from the fully relaxed interface in the supercell, and then recalculate the electronic structure self-consistently keeping the atom s xed. The quantity h n (z)i thus indicates the change in electron density resulting from chemical

TABLE II. A dhesion energy (ideal work of separation) W of the Cu/ -cristobalite(001) interfaces.

	W	(J/m <sup>2</sup> )
Sitem inated		1.406
0-term inated		1.555
00-term inated		3.805

bonding between the Cu layers and the SiD<sub>2</sub> substrate. (To simplify the analysis, we are neglecting additional changes stemming from the atomic rearrangements at the free surfaces of SiD<sub>2</sub> and Cu.) The results of calculations of the h n (z)i appear in Fig. 4. The h n (z)i in the 00 -term inated casem ost prominently deviates from zero around the interface, recting signi cant charge transfer between the two slabs. The charge transfer in the 0 - and Si-term inated cases is comparatively much smaller. In particular, in the Si-term inated case, the depletion of the density in the vicinity of the low est Cu layer is not so drastic, suggesting that the localized Cu d states have less in uence on the bonding around the interface.

### C.Quantitative analysis of adhesion

To assess the adhesive strength of the interfaces, we have calculated the idealwork of separation, or adhesion energy, per unit area W from

W 
$$(E_{SiO_2} + E_{Cu} - E_{IF}) = A;$$

where  $E_{SiO_2}$ ,  $E_{Cu}$ , and  $E_{IF}$  are the energies of the isolated SiO<sub>2</sub> substrate, Cu layers, and Cu/SiO<sub>2</sub> interface in



FIG.5. A dhesion energy as a function of the position of Cu layers in the xy plane calculated for ve di erent initial positions and for each of the three term inations. Each point is obtained by translating Cu layers [initially positioned on the substrate as described in Sec. IV A (x = 0; y = 0)] in the xy plane by (x; y) and then fully relaxed. The abscissa (which quanti es the m agnitude of the shift of Cu layers) is scaled by the supercell lattice parameter a = 5 A.

the supercell, respectively, and A is the area. Physically, the adhesion energy W is the work per unit area required to separate the interface into the C u layers and the SiO  $_2$ substrate within a microcanonical process, and it can be considered a measure of the strength of the adhesion. For the purposes of comparison, all energies are calculated using supercells of the same size (5 A 5 A 30 A) independent of whether it contains Cu layers, any of the  $SiO_2$  substrates, or  $Cu/SiO_2$  interfaces. Table II lists the adhesion energy for each case. The adhesion energy in the 00-term inated case turns out to be much larger than those in the 0- and Sitem inated cases, and com parable to values previously com puted for other m etal-dielectric interfaces, such as Co/TiC (R ef. 21) and  $Nb/AbO_3$  (Ref. 22). We note that the computed energies for the 0.0 -term inated case,  $4 \text{ J/m}^2$ , are consistent with values obtained experimentally by Kriese et al.6 for 100 nm thick  $\text{Im s of Cu on SiD}_2$  using an indentation technique. In sum m ary, the m agnitudes of adhesion energies computed here for each of the three di erent interfaces re ect the trends witnessed above in their structural and bonding properties.

## 1. Local atom ic structure

At this point, it is meaningful to investigate further a drawback of using crystalline cristobalite to model the am orphous substrate. When Cu layers are placed on an am orphous SiO<sub>2</sub> substrate, di erent localatom ic con-



FIG. 6. Structures at the 00 -term inated interfaces obtained as a function of initial positions of Cu layers with respect to the substrate. The gures within brackets denote the shift of the position of Cu layers within the xy plane (see the caption of Fig. 5) in unit of 5 A (the in-plane supercell lattice parameter).

gurations are possible at the interfaces because of the non-periodicity of glass. A principal sim pli cation of our m odel is the imposition of translational symmetry: we are unable to directly assess the di erence between the adhesive properties of crystalline substrates and those of am orphous substrates. We are, how ever, able to investigate the sensitivity of our calculated adhesion energies to changes in local atom ic structure. As a rst step, we com pute the in uence of the position of Cu layers, relative to the substrate, on the adhesion energy by translating the Cu layers in the xy plane.

A s shown in F ig 5, the adhesion energy turns out rather insensitive to the initial position of the Cu layers so long as the term ination type remains unchanged. This result suggests that the adhesive properties realized in these

cristobalite substrates m ay well be carried over, to som e extent, to those of glass substrates. The insensitivity of adhesion energy to the position of C u layers does not im ply that the detailed structure at the interface is less im portant for adhesion. In fact, as shown in F ig. 6 for the 00 -term inated case, atom s at the interfaces do m ove signi cantly relative to the unshifted case. Since the surface atom s have a greater freedom to choose their position than those in bulk, the adhesion energy rem ains rather constant for various initial positions of C u layers.

#### 2. Local oxygen surface coverage

Thus far we have investigated the Si-, 0 -, and 00 - term inations independently. Depending on the oxygen partial pressure, however, these term inations are generally expected to coexist on the substrate surface, independent of whether the substrate is crystalline or am orphous. To exam ine the e ects of oxygen surface densi-



FIG.7. A dhesion energy as a function of oxygen density at the substrate surface.<sup>44</sup> The densities 0, 2, 4, 6, and 8 nm <sup>2</sup> correspond to the Si-, (SiO)-, O-, (O,OO)-, OO-term inated cases, respectively.

ties interm ediate between those of the Si-, 0-, and 00term inated cases, we enlarge the supercell by a factor of two along the y-axis (along the horizontal direction of Figs. 1, 2, and 6). For the 1 2-supercells, three new surfaces, in addition to those already considered above, are now possible. These are: a (Si,O)-term inated surface which consists of neighboring Si- and O -term inated surfaces; a (Si,00)-term inated surface which consists of neighboring Si- and 00-term inated surfaces; and a (0,00)-term inated surface which consists of neighboring 0-and 00-term inated surfaces. Note that the (Si,00)term inated case possesses the same oxygen density as the 0-term inated case.] We nd that the (Si,00)-term inated substrate has energy which is higher than that of the 0term inated surface by 1:4 eV per Siatom at the surface (per 25 A<sup>2</sup>). Therefore, we restrict our focus to investigation of the (Si,O)-and (O,OO)-term inated cases, calculating their relaxed structures and adhesion energies.

F igure 7 depicts the adhesion energy as a function of the oxygen density at the interface. Rem arkably, the adhesion energy is not a monotonically-increasing function of oxygen density; at low oxygen density, increasing the number of 0 atoms a small amount does not necessarily lead to stronger adhesion. However, beyond the oxygen density of 4 nm<sup>2</sup> where the 00-term ination will begin to appear appreciably, the adhesion energy increases, and does so alm ost linearly. This linear dependence in plies that each 00 surface unit contributes to the adhesion fairly independently, and thus the locally 00-term inated regions may not necessarily have to form large dom ains in order to work as an elective \glue", although it is clear that a critical density of such locally 00-term inated regions is required for strong adhesion.



FIG.8. Relaxed structures of the  $0\,H\,O\,H$  -term insted surface and interface.

### 3. Hydroxylated surfaces

W e now address a frequently-cited reason for the weak adhesion at  $Cu/a-SiO_2$  interfaces, namely the existence of hydroxyl groups on the SiO  $_2$  surface.<sup>7</sup> It is well know n that hydroxyls are likely to form on the SiO<sub>2</sub> surface under \wet" deposition conditions; to exam ine the impact of hydroxyls on adhesion from rst-principles, we add two hydrogens to the 1 100-term inated surface, and relax all of the atom s. The result is that the cohesive energy of OHOH-term inated substrate, in which a Siatom is term insted by two hydroxyls, is lower than that of 00 term inated substrate by 112 eV per surface Siatom. This energy di erence is much larger than the dissociation energy of  $H_2$  molecule ( 4:5 eV per molecule), suggesting the high stability of the OHOH-term inated substrate. If we now place the Cu layers on top of the hydroxylated surface and relax the interface (Fig. 8), we

nd that the deposition of C u layers does not signi cantly a ect the structure at the O H O H -term inated surface, im – plying little interaction; the hydrogen present at the surface leaves the surface neutral and inert. This tendency is clearly re ected in the calculated adhesion energy, and according to our calculations it is just 0.331 J/m<sup>2</sup>, less than one tenth of the adhesion energy observed in the O O -term inated case.

However, as shown in Table II, the adhesion energies for all other cases studied here (i.e. the 00-, 0-, and Si-term inated cases) seem to be of a magnitude which should produce adhesion, especially the oxygenrich 0.0 -term inated case. It is also noteworthy that the 0.0 -term inated substrate, which has the largest adhesion energy among the three, looks actually the most stable substrate. These facts in ply that should dehydroxylation of the substrate surfaces be successfully achieved (e.g. by annealing or particle bom bardment of a growing Im surface), robust adhesion is entirely possible, at least from

the point of view of chem ical bonding.

# V.CONCLUSIONS

We have performed a rst-principles study of the adhesive properties of atom ically-sharp Cu/SiD<sub>2</sub> interfaces. As a model a-SiO<sub>2</sub> substrate, we used a crystalline polymorph of  $SiO_2$ , cristobalite, and investigated its Si-, 0-, and 00-term inated (001) surfaces in detail. For interfaces between Cu and OO-term inated surfaces, a substantial rearrangem ent of oxygen positions relative to the free surface is observed, suggesting the form ation of strong Cu-O bonds. A nalysis of the local density of states at the interface show ed that Cu-O interfacial bonds are composed of Cu d and O p states. The computed adhesion energy also exhibited a tendency toward much stronger adhesion in the 00-term inated interface than in the O-and Sitem inated interfaces: Substrate surfaces with high oxygen content were found suitable for adhesion.

The adhesion energy is found to be very insensitive to the position of the Cu layers if the term ination type is unchanged, and this observation suggests that

cristobalite m ay serve as a good starting m odel of  $a-SiO_2$  substrates. The detailed dependence of the adhesion energy on oxygen density at the substrate surface has been investigated, and it shows that the surfaces where the O- and OO -term inations coexist can also lead to relatively strong adhesion.

The possible existence of hydroxyl groups at the substrate surface is thought to be the main cause for the weak adhesion observed in experiment. However, if these hydroxyls are removed beforehand and the oxygen density at the surface is increased (for example, by upping the oxygen partial pressure), Cu layers are predicted to adhere reasonably well to  $SiO_2$ . In addition to the possibility of direct comparison to future measurements on crystalline Cu/-cristobalite(001) interfaces, these results should serve as a starting point for which to study more complicated interfacial geometries, benchmarks for future investigations, and a baseline for experiments attempting to elucidate complicated phenomena a ecting adhesion at Cu/glass interfaces.

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